Amendment To The Claims

1. (Previously Presented) A method for joining a semiconductor die to a leadframe comprising the steps of:

providing a semiconductor die and a leadframe;

forming at least three pedestals raised above a surface of said leadframe in a mounting area adapted for receiving said semiconductor die attached thereto, each of said pedestals having substantially the same pedestal height;

introducing solder onto said mounting area;

heating to urge said solder to deform and to include an average thickness being at least as great as said pedestal height; and

joining said semiconductor die to said mounting area and urging said solder to solidify, such that said semiconductor die contacts each of said pedestals and said solder.

2. (Original) The method as in claim 1, further comprising the step of heating to urge said adhesive material to deform and in which said step of joining includes urging said adhesive material to solidify.

3. (Previously Presented) The method as in claim 1, in which said solder comprises a tin/lead eutectic.

4. (Previously Presented) The method as in claim 1, in which said solder comprises a silver alloy.

5. (Original) The method as in claim1, in which said pedestals each include a height within the range of 1-2 mils.

6. (Original) The method as in claim 1, wherein said leadframe is formed of a malleable material and said step of forming comprises mechanically stamping said leadframe to form said pedestals as integral portions of said leadframe which protrude from said surface.

7. (Original) The method as in claim 1, in which each of said pedestals includes a shape being one of cylindrical and conical.

8. (Previously Presented) The method as in claim 1, in which said step of providing includes providing said semiconductor die having a top including a semiconductor device formed thereon, sides and a bottom for contacting said pedestals, and in which said step of introducing includes introducing sufficient solder such that said heating and joining urges portions of said solder to extend at least partially along said sides of said semiconductor die when said bottom contacts said pedestals.

9. (Original) The method as in claim 1, in which said semiconductor die includes an integrated circuit formed on a top surface thereof, and said step of joining includes joining a bottom surface of said die to said leadframe such that said bottom surface contacts each of said pedestals.

10. (Original) A method for joining a semiconductor chip to a leadframe comprising the steps of:

providing a leadframe and a semiconductor chip;

forming a least three pedestals raised above a surface of said leadframe in a mounting area adapted for receiving said semiconductor chip attached thereto; each of said pedestals having substantially the same pedestal height;

introducing a viscous solder material onto said mounting area; and

joining said semiconductor chip to said mounting area of said leadframe such that said semiconductor chip contacts each of said pedestals and said solder.

11. (Previously Presented) An assembly comprising a semiconductor die attached to a surface of a leadframe by solder, said leadframe including at least three pedestals one of protruding from and formed over said surface, each of said pedestals having substantially the same pedestal height; and said semiconductor die contacting each of said pedestals.

12. (Original) The assembly as in claim 11, in which said pedestal height lies within the range of 1-2 mils.

13. (Original) The assembly as in claim 11, in which said pedestals each include a top portion which contacts said semiconductor die and said top portion includes an area within the range of 490 micron^2 and 2000 micron^2 .

14 (Original) The assembly as in claim 11, in which each of said pedestals are conical in shape and include a base coincident with said surface and an apex which contacts said semiconductor die.

15. (Cancel) The assembly as in claim 11, in which said solder comprises a tin/lead eutectic.

16. (Original) The assembly as in claim 11, wherein said pedestals each comprise raised portions of said leadframe.

17. (Original) The assembly as in claim 11, wherein each of said pedestals are discrete members joined to said surface.

18. (Original) The assembly as in claim 11, wherein said leadframe is formed of copper.

19. (Cancel) The assembly as in claim 11, wherein said solder comprises silver alloy.

20. (Original) The assembly as in claim 11, wherein said pedestals are substantially cylindrical in shape and include substantially flat tops which contact said semiconductor die.

21. (Previously Presented) The assembly as in claim 11, in which said semiconductor die includes an integrated circuit formed thereon, an opposed bottom surface contacting said solder and said pedestals and facing said leadframe, and sides, and said solder extends at least partially up said sides.

22. (Previously Presented) The assembly as in claim 11, in which said solder laterally surrounds each of said pedestals and is interposed between said semiconductor die and said surface, has a thickness substantially equal to said pedestal height, and therefore contacts said semiconductor die and said leadframe.

23. (Previously Presented) The assembly as in claim 22, in which said semiconductor die includes a top surface including circuitry thereon, an opposed bottom surface contacting said solder and said pedestals and facing said leadframe, and sides, and said solder extends at least partially up said sides.

24 (Previously Presented) The assembly as in claim 22, in which said solder is characterized as being void-free between said semiconductor die and said surface.